

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4913	optical adj wave adj guide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 08:14
L2	8122	cmos and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 08:15
L3	49	L2 and 1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 08:15
L4	4450	germanium adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 08:16
L5	23	1 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 08:16
S1	0	cmos and sacrificial adj germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 07:32
S2	4838	cmos and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 09:17
S3	367	epitaxial adj layer near germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 09:17
S4	6	"5126805".URPN.	USPAT	OR	ON	2004/09/02 09:31

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S5	192	selective adj deposition and (sige or silicon adj germanium) and (epitaxial or epitaxy or epitaxially) and (mask or photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 11:12
S6	118	(mos or mosfet or cmos) and (selective adj deposition and (sige or silicon adj germanium) and (epitaxial or epitaxy or epitaxially) and (mask or photoresist))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:18
S7	61	implanting adj germanium and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/02 12:20
S8	2	("6445016").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/02 12:20
S9	2854	germanium adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 10:59
S10	4548	germanium adj layer or germanium adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 10:26
S11	1718	alloy and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 10:27
S12	887	gate adj electrode and S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 10:27

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S13	537	silicon adj substrate and S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 10:27
S14	1374	silicon adj germanium adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 10:27
S15	388	S13 and S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 10:27
S16	3	("5624869" "5883003" "6037922").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/23 10:54
S17	11	("6214679").URPN.	USPAT	OR	ON	2005/07/23 10:54
S18	50	germanium adj layer and polysilicon adj gate adj electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/23 11:00
S19	427	(438/31).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/25 07:59
S20	0	((ge or germanium) and clad and sio and (b or boron) and refractive adj index).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/25 08:00